



**ZXMP6A17G**

**60V P-CHANNEL ENHANCEMENT MODE MOSFET**

**Product Summary**

$V_{(BR)DSS}$	$R_{DS(on)}$	$I_D$ $T_A = 25^\circ C$
-60V	125mΩ @ $V_{GS} = -10V$	-4.3A
	190mΩ @ $V_{GS} = -4.5V$	-3.5A

**Description and Applications**

This MOSFET has been designed to minimize the on-state resistance and yet maintain superior switching performance, making it ideal for high efficiency power management applications.

- Motor control
- DC-DC Converters
- Power management functions
- Uninterrupted power supply

**Features and Benefits**

- Fast switching speed
- Low gate drive
- Low input capacitance
- “Green” component and RoHS compliant (Note 1)
- Qualified to AEC-Q101 Standards for High Reliability

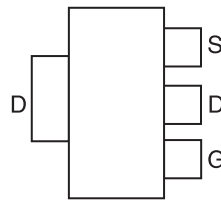
**Mechanical Data**

- Case: SOT-223
- Case Material: Molded Plastic, UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish - Matte Tin annealed over Copper lead frame. Solderable per MIL-STD-202, Method 208
- Weight: 0.112 grams (approximate)

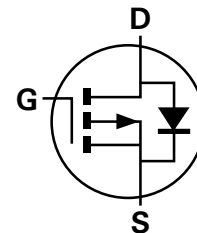
SOT223



Top View



Pin Out - Top View



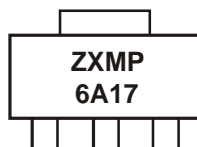
Equivalent Circuit

**Ordering Information** (Note 1)

Product	Marking	Reel size (inches)	Tape width (mm)	Quantity per reel
ZXMP6A17GTA	See below	7	12	1,000

Note: 1. Diodes, Inc. defines “Green” products as those which are RoHS compliant and contain no halogens or antimony compounds; further information about Diodes Inc.’s “Green” Policy can be found on our website. For packaging details, go to our website.

**Marking Information**



ZXMP = Product Type Marking Code, Line 1  
6A17 = Product Type Marking Code, Line 2

**Maximum Ratings** @ $T_A = 25^\circ\text{C}$  unless otherwise specified

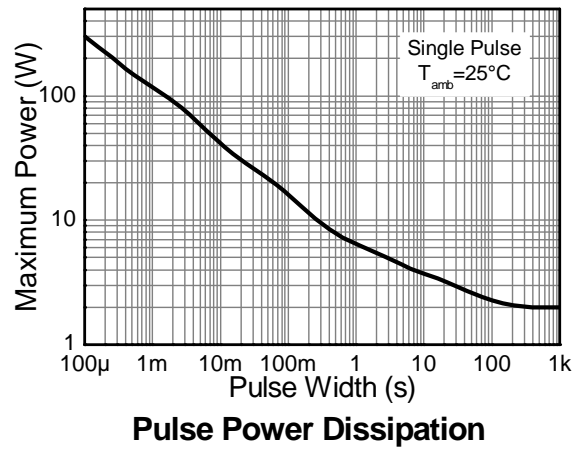
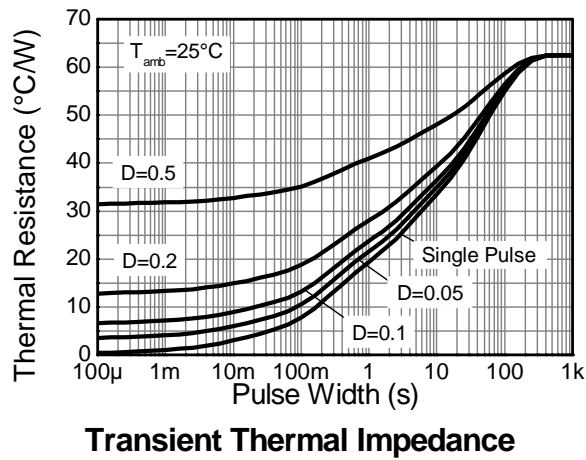
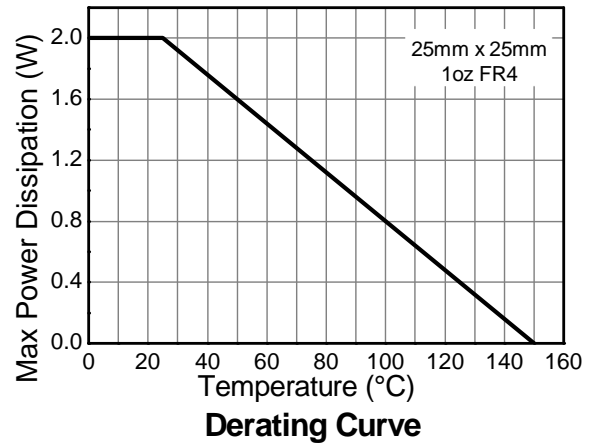
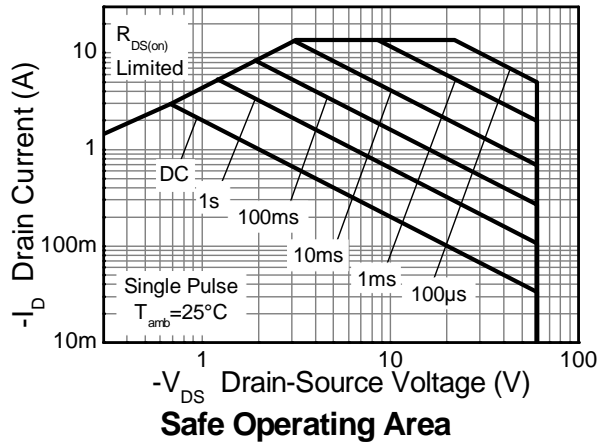
Characteristic			Symbol	Value	Unit	
Drain-Source voltage			$V_{DSS}$	-60	V	
Gate-Source voltage			$V_{GS}$	$\pm 20$	V	
Continuous Drain current	$V_{GS} = 10\text{V}$	(Note 3)	$I_D$	-4.3	A	
		$T_A = 70^\circ\text{C}$ (Note 3)		-3.5		
		(Note 2)		-3.0		
Pulsed Drain current	$V_{GS} = 10\text{V}$	(Note 4)	$I_{DM}$	-13.7	A	
Continuous Source current (Body diode)			(Note 3)	$I_S$	-4.8	A
Pulsed Source current (Body diode)			(Note 4)	$I_{SM}$	-13.7	A

**Thermal Characteristics** @ $T_A = 25^\circ\text{C}$  unless otherwise specified

Characteristic		Symbol	Value	Unit
Power dissipation	(Note 2)	$P_D$	2.0	W
			16	
Linear derating factor	(Note 3)		3.9	$\text{mW}/^\circ\text{C}$
			31	
Thermal Resistance, Junction to Ambient	(Note 2)	$R_{\theta JA}$	62.5	$^\circ\text{C}/\text{W}$
	(Note 3)		32.0	
Thermal Resistance, Junction to Lead	(Note 5)	$R_{\theta JL}$	9.8	$^\circ\text{C}/\text{W}$
Operating and storage temperature range		$T_J, T_{STG}$	-55 to 150	$^\circ\text{C}$

- Notes:
2. For a device surface mounted on 25mm x 25mm x 1.6mm FR4 PCB with high coverage of single sided 1oz copper, in still air conditions; the device is measured when operating in a steady-state condition.
  3. Same as note (2), except the device is measured at  $t \leq 10$  sec.
  4. Same as note (2), except the device is pulsed with  $D = 0.02$  and pulse width 300  $\mu\text{s}$ . The pulse current is limited by the maximum junction temperature.
  5. Thermal resistance from junction to solder-point (at the end of the drain lead).

**Thermal Characteristics**

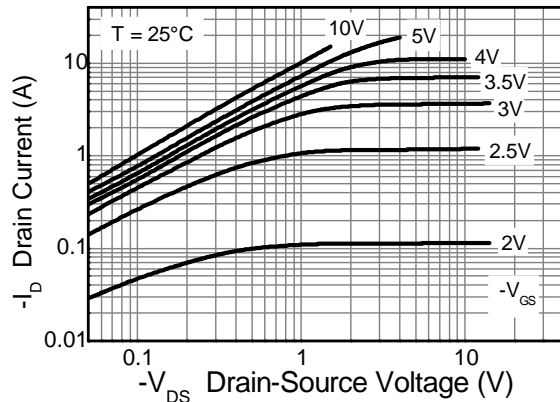


**Electrical Characteristics** @ $T_A = 25^\circ\text{C}$  unless otherwise specified

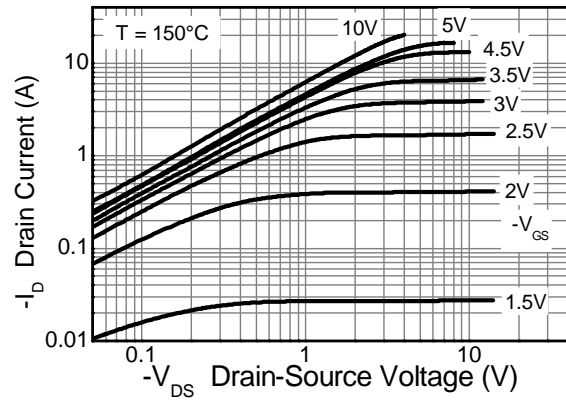
Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
<b>OFF CHARACTERISTICS</b>						
Drain-Source Breakdown Voltage	$BV_{DSS}$	-60	—	—	V	$I_D = -250\mu\text{A}$ , $V_{GS} = 0\text{V}$
Zero Gate Voltage Drain Current	$I_{DSS}$	—	—	-0.5	$\mu\text{A}$	$V_{DS} = -60\text{V}$ , $V_{GS} = 0\text{V}$
Gate-Source Leakage	$I_{GSS}$	—	—	$\pm 100$	nA	$V_{GS} = \pm 20\text{V}$ , $V_{DS} = 0\text{V}$
<b>ON CHARACTERISTICS</b>						
Gate Threshold Voltage	$V_{GS(th)}$	-1.0	—	—	V	$I_D = -250\mu\text{A}$ , $V_{DS} = V_{GS}$
Static Drain-Source On-Resistance (Note 6)	$R_{DS(on)}$	—	0.096	0.125	$\Omega$	$V_{GS} = -10\text{V}$ , $I_D = -2.2\text{A}$
			0.120	0.190		$V_{GS} = -4.5\text{V}$ , $I_D = -1.8\text{A}$
Forward Transconductance (Notes 6 & 7)	$g_{fs}$	—	4.7	—	S	$V_{DS} = -15\text{V}$ , $I_D = -2.2\text{A}$
Diode Forward Voltage (Note 6)	$V_{SD}$	—	-0.85	-0.95	V	$I_S = -2.0\text{A}$ , $V_{GS} = 0\text{V}$ , $T_J = 25^\circ\text{C}$
Reverse recovery time (Note 7)	$t_{rr}$	—	25.1	—	ns	$I_S = -1.7\text{A}$ , $di/dt = 100\text{A}/\mu\text{s}$ , $T_J = 25^\circ\text{C}$
Reverse recovery charge (Note 7)	$Q_{rr}$	—	27.2	—	nC	$T_J = 25^\circ\text{C}$
<b>DYNAMIC CHARACTERISTICS (Note 7)</b>						
Input Capacitance	$C_{iss}$	—	637	—	pF	$V_{DS} = -30\text{V}$ , $V_{GS} = 0\text{V}$ $f = 1\text{MHz}$
Output Capacitance	$C_{oss}$	—	70.0	—	pF	
Reverse Transfer Capacitance	$C_{rss}$	—	53.0	—	pF	
Total Gate Charge (Note 8)	$Q_g$	—	9.0	—	nC	$V_{GS} = -4.5\text{V}$
Total Gate Charge (Note 8)	$Q_g$	—	17.7	—	nC	$V_{GS} = -10\text{V}$
Gate-Source Charge (Note 8)	$Q_{gs}$	—	1.6	—	nC	
Gate-Drain Charge (Note 8)	$Q_{gd}$	—	4.4	—	nC	
Turn-On Delay Time (Note 8)	$t_{D(on)}$	—	2.6	—	ns	$V_{DD} = -30\text{V}$ , $V_{GS} = -10\text{V}$ $I_D = -1\text{A}$ , $R_G \cong 6.0\Omega$
Turn-On Rise Time (Note 8)	$t_r$	—	3.4	—	ns	
Turn-Off Delay Time (Note 8)	$t_{D(off)}$	—	26.2	—	ns	
Turn-Off Fall Time (Note 8)	$t_f$	—	11.3	—	ns	

- Notes:
6. Measured under pulsed conditions. Pulse width  $\leq 300\mu\text{s}$ ; duty cycle  $\leq 2\%$
  7. For design aid only, not subject to production testing.
  8. Switching characteristics are independent of operating junction temperatures.

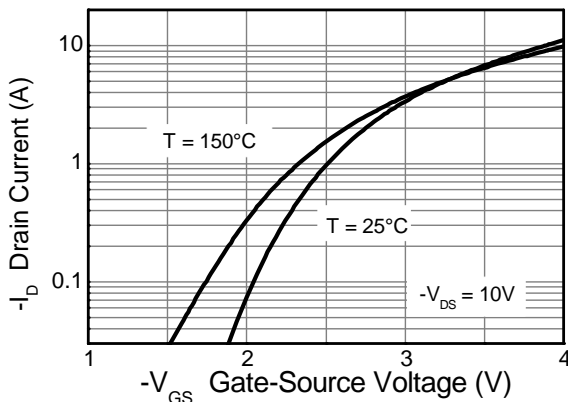
**Typical Characteristics**



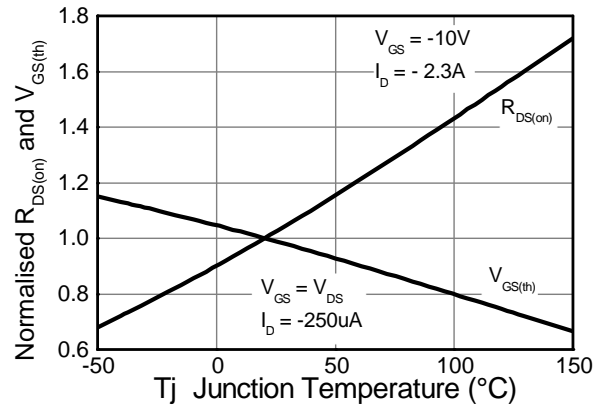
**Output Characteristics**



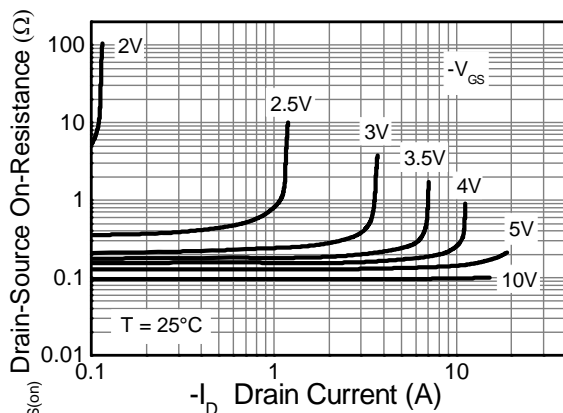
**Output Characteristics**



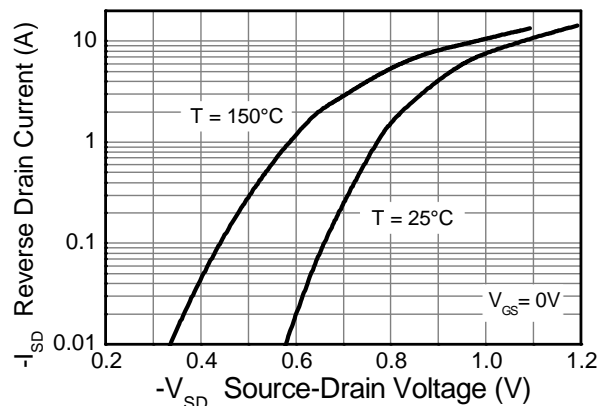
**Typical Transfer Characteristics**



**Normalised Curves v Temperature**

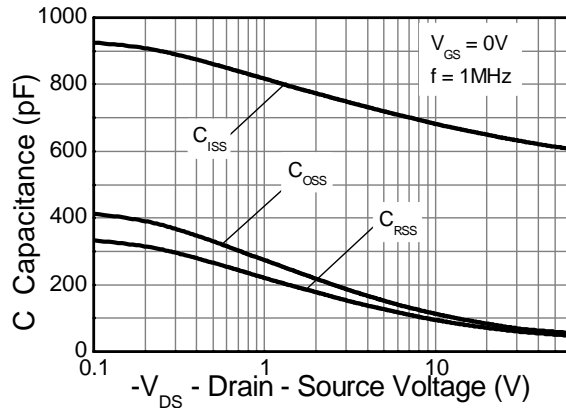


**On-Resistance v Drain Current**

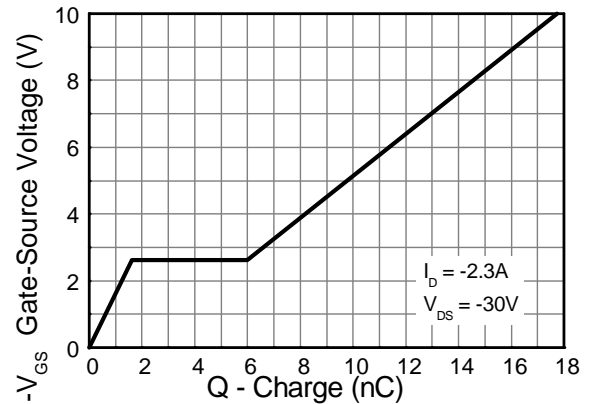


**Source-Drain Diode Forward Voltage**

**Typical Characteristics – continued**

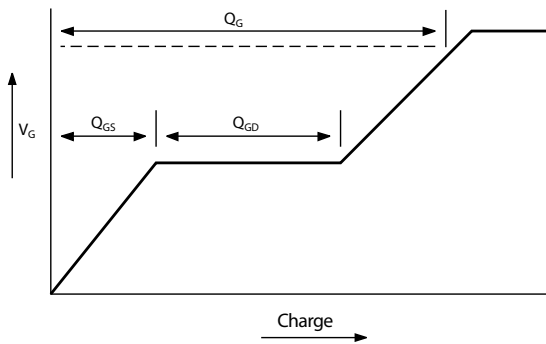


**Capacitance v Drain-Source Voltage**

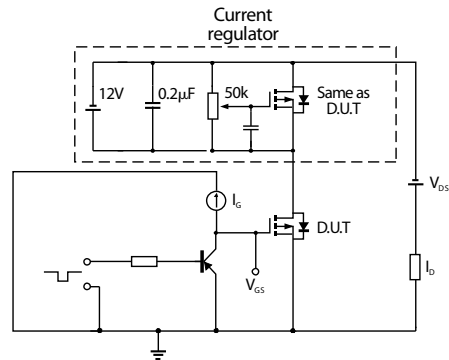


**Gate-Source Voltage v Gate Charge**

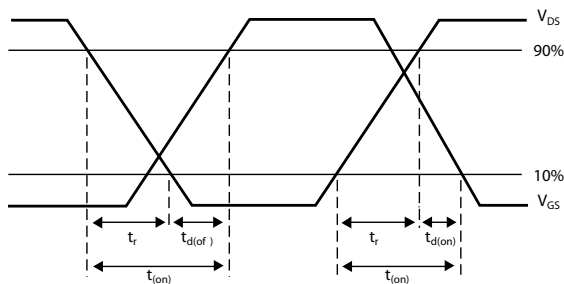
**Test Circuits**



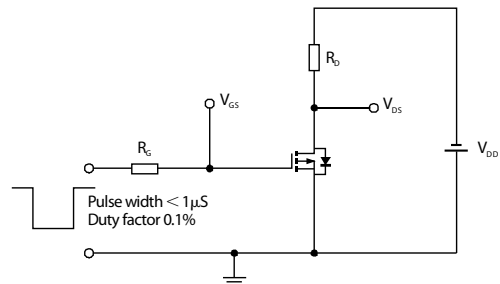
**Basic gate charge waveform**



**Gate charge test circuit**

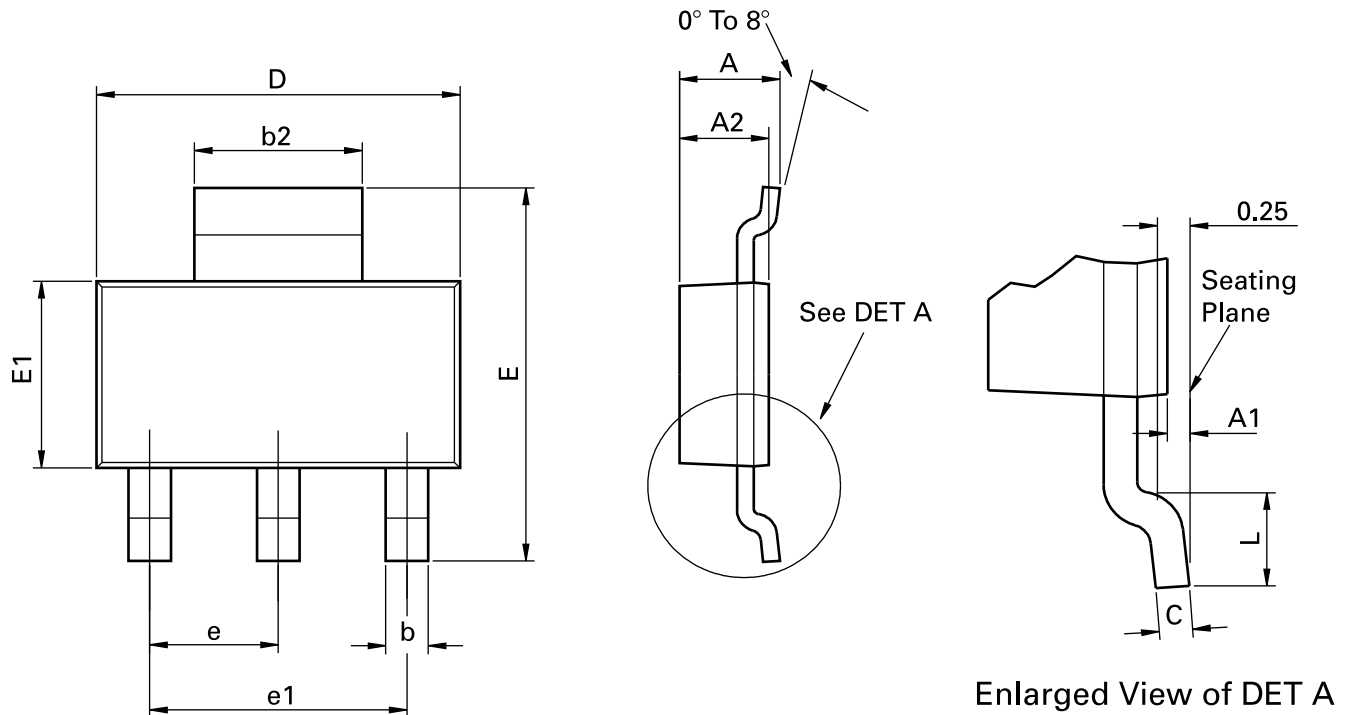


**Switching time waveforms**



**Switching time test circuit**

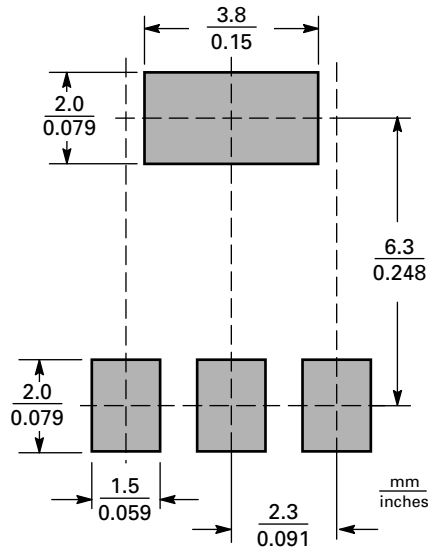
**Package Outline Dimensions**



Conforms to JEDEC TO-261 AA Issue B

DIM	Millimeters		Inches		DIM	Millimeters		Inches	
	Min	Max	Min	Max		Min	Max	Min	Max
A	-	1.80	-	0.071	D	6.30	6.70	0.248	0.264
A1	0.02	0.10	0.0008	0.004	e	2.30 BSC		0.0905 BSC	
A2	1.55	1.65	0.0610	0.0649	e1	4.60 BSC		0.181 BSC	
b	0.66	0.84	0.026	0.033	E	6.70	7.30	0.264	0.287
b2	2.90	3.10	0.114	0.122	E1	3.30	3.70	0.130	0.146
C	0.23	0.33	0.009	0.013	L	0.90	-	0.355	-

**Suggested Pad Layout**



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- Защиту от снятия компонента с производства.
- Оценку стоимости проекта по компонентам.
- Изготовление тестовой платы монтаж и пусконаладочные работы.



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